

HiPerRF™ Power MOSFETs

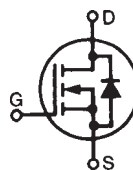
F-Class: MegaHertz Switching

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , Low Intrinsic R_g
High dV/dt , Low t_{rr}

IXFX 55N50F
IXFK 55N50F

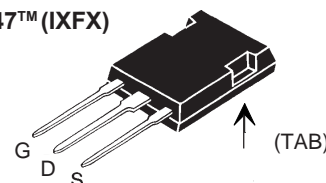
$V_{DSS} = 500 \text{ V}$
 $I_{D25} = 55 \text{ A}$
 $R_{DS(on)} = 85 \text{ m}\Omega$

$t_{rr} \leq 250 \text{ ns}$

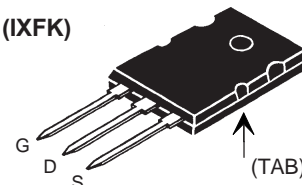


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	55	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	220	A
I_{AR}	$T_C = 25^\circ\text{C}$	55	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	3.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	560	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	TO-264	0.4/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS 247™ (IXFX)



TO-264 AA (IXFK)



G = Gate D = Drain
S = Source TAB = Drain

Features

- RF capable Mosfets
- Rugged polysilicon gate cell structure
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance - easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

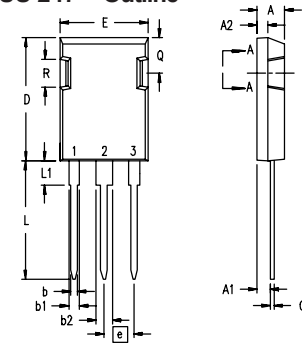
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		100 μA
		$T_J = 125^\circ\text{C}$		3 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Note 1			85 m Ω

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 • I _{D25} Note 1	22	33	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		6700	pF
C_{oss}			1250	pF
C_{rss}			330	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 1 Ω (External)		24	ns
t_r			20	ns
t_{d(off)}			45	ns
t_f			9.6	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		195	nC
Q_{gs}			50	nC
Q_{gd}			95	nC
R_{thJC}			0.21	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode		Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			55 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			220 A
V_{SD}	I _F = 25A, V _{GS} = 0 V, Note 1			1.5 V
t_{rr}	I _F = 25A, -di/dt = 100 A/μs, V _R = 100 V			250 ns
Q_{RM}			1.0	μC
I_{RM}			10	A

Note: 1. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

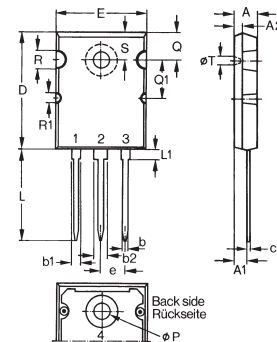
PLUS 247™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

Fig. 1. Output Characteristics at 25°C

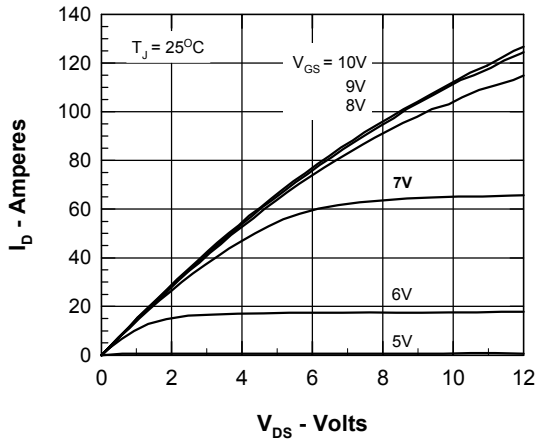


Fig. 2. Output Characteristics at 125°C

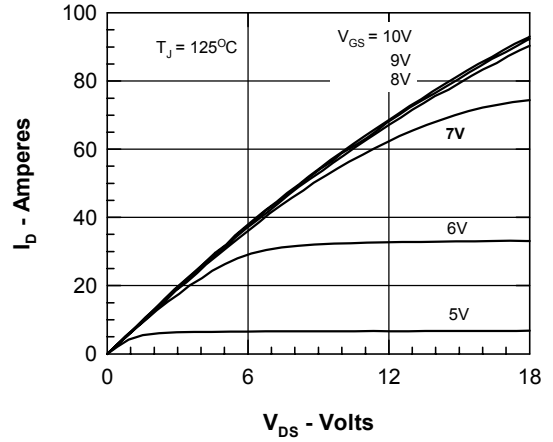


Fig. 3. $R_{DS(ON)}$ vs. Drain Current

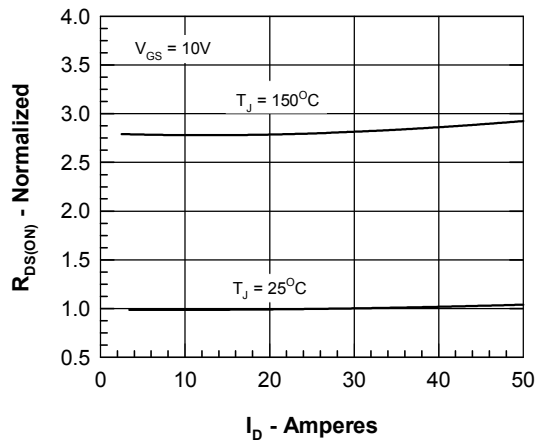


Fig. 4. $R_{DS(ON)}$ vs. T_J

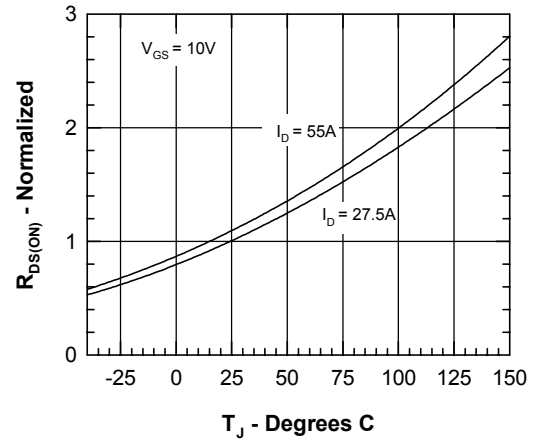


Fig. 5. Drain Current vs. Case Temperature

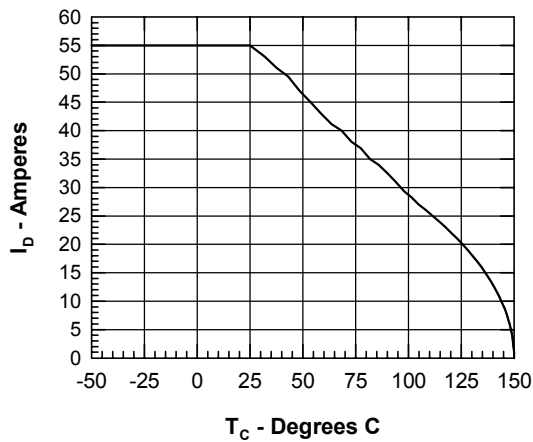


Fig. 6. Admittance Curves

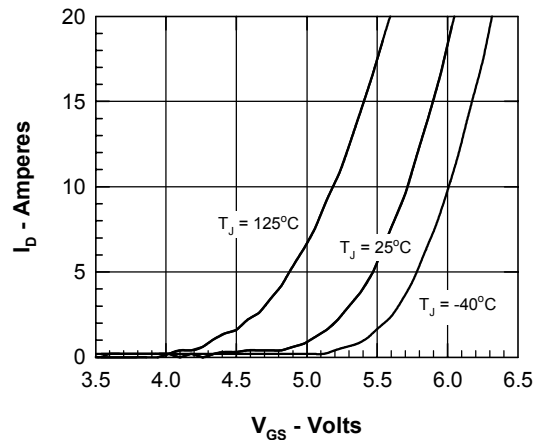


Fig. 7. Gate Charge Characteristic Curve

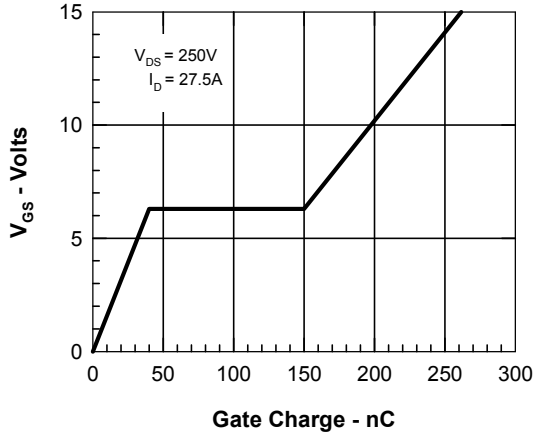


Fig. 8. Capacitance Curves

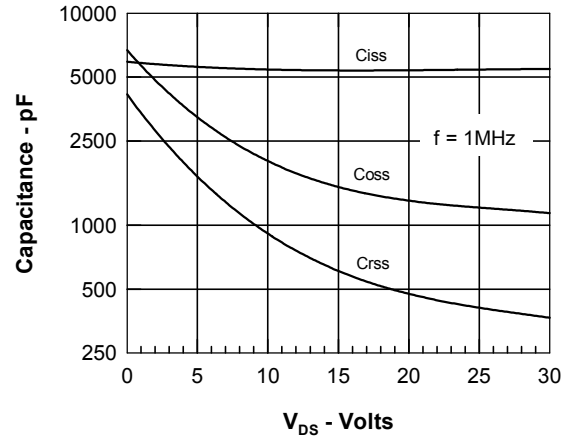


Fig. 9. Source Current vs. Source to Drain Voltage

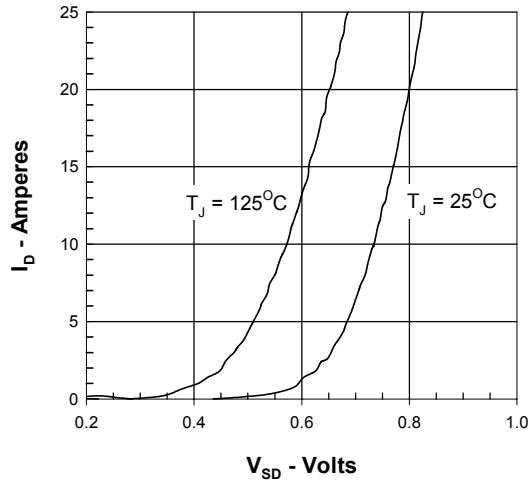
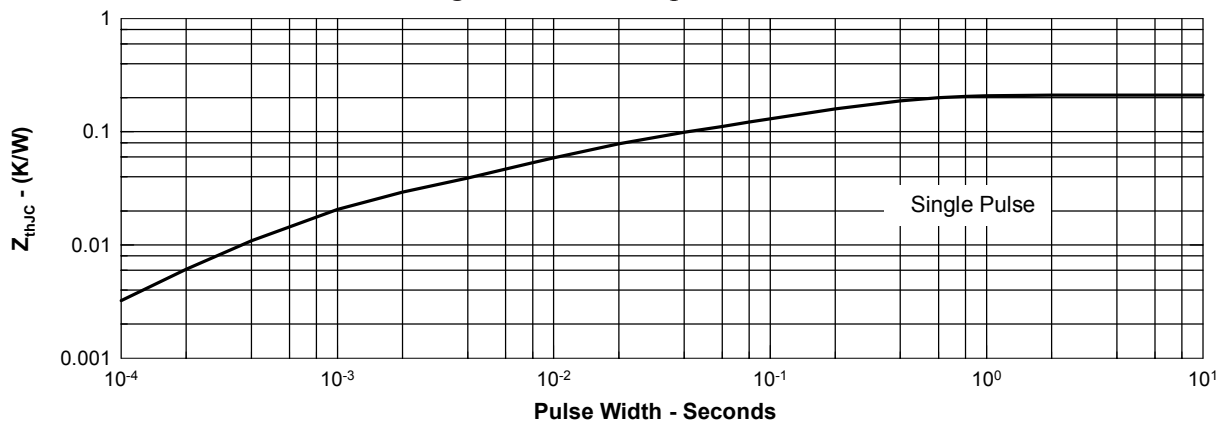


Fig. 10. Thermal Impedance



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